ON Semiconductor®



# 6 and 8-Channel Low Capacitance ESD Protection Arrays

CM1213

#### **Features**

- 6 or 8 channels of ESD protection
  - Note: For 1, 2, and 4 channel devices, see the CM1213A datasheet.
- Provides ESD protection to IEC61000-4-2 Level 4
  - ±8kV contact discharge
- Low channel input capacitance of 1.0pF typical
- Minimal capacitance change with temperature and voltage
- Channel input capacitance matching of 0.02pF typical is ideal for differential signals
- Mutual capacitance between signal pin and adjacent signal pin -0.11pF typical
- Zener diode protects supply rail and eliminates the need for external by-pass capacitors
- Each I/O pin can withstand over 1000 ESD strikes\*
- Available in SOIC and MSOP, lead-free packaging

## **Applications**

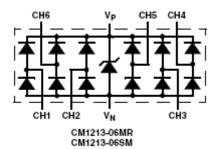
- USB2.0 ports at 480Mbps in desktop PCs, notebooks and peripherals
- IEEE1394 Firewire® ports at 400Mbps / 800Mbps
- DVI ports, HDMI ports in notebooks, set top boxes, digital TVs, LCD displays
- Serial ATA ports in desktop PCs and hard disk drives
- PCI Express ports
- General purpose high-speed data line ESD protection

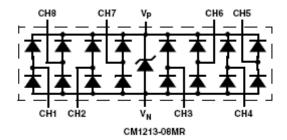
## **Product Description**

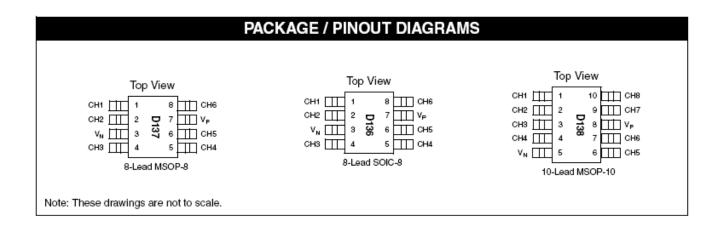
The CM1213 family of diode arrays has been designed to provide ESD protection for electronic components or sub-systems requiring minimal capacitive loading. These devices are ideal for protecting systems with high data and clock rates or for circuits requiring low capacitive loading. Each ESD channel consists of a pair of diodes in series which steer the positive or negative ESD current pulse to either the positive  $(V_{\scriptscriptstyle R})$  or negative  $(V_{\scriptscriptstyle N})$ supply rail. A Zener diode is embedded between V<sub>P</sub> and  $V_N$ , offering two advantages. First, it protects the V<sub>cc</sub> rail against ESD strikes, and second, it eliminates the need for a bypass capacitor that would otherwise be needed for absorbing positive ESD strikes to ground. The CM1213 will protect against ESD pulses up to ±8kV per the IEC 61000-4-2 standard.

These devices are particularly well-suited for protecting systems using high-speed ports such as USB2.0, IEEE1394 (Firewire®, iLink<sup>TM</sup>), Serial ATA, DVI, HDMI and corresponding ports in removable storage, digital camcorders, DVD-RW drives and other applications where extremely low loading capacitance with ESD protection are required in a small package footprint.

#### **Block Diagram**







# **Pin Descriptions**

	PIN DESCRIPTIONS						
	6-CHANNEL, 8-LEAD MSOP-8/SOIC-8 PACKAGES						
PIN	NAME	TYPE	DESCRIPTION				
1	CH1	I/O	ESD Channel				
2	CH2	I/O	ESD Channel				
3	V <sub>N</sub>	GND	Negative voltage supply rail				
4	CH3	I/O	ESD Channel				
5	CH4	I/O	ESD Channel				
6	CH5	I/O	ESD Channel				
7	V <sub>P</sub>	PWR	Positive voltage supply rail				
8	CH6	I/O	ESD Channel				

	PIN DESCRIPTIONS						
	8-CHANNEL, 10-LEAD MSOP-10 PACKAGE						
PIN	NAME	ТҮРЕ	DESCRIPTION				
1	CH1	I/O	ESD Channel				
2	CH2	I/O	ESD Channel				
3	CH3	I/O	ESD Channel				
4	CH4	I/O	ESD Channel				
5	V <sub>N</sub>	GND	Negative voltage supply rail				
6	CH5	I/O	ESD Channel				
7	CH6	I/O	ESD Channel				
8	V <sub>P</sub>	PWR	Positive voltage supply rail				
9	CH7	I/O	ESD Channel				
10	CH8	I/O	ESD Channel				

# **Ordering Information**

PART NUMBERING INFORMATION					
Lead-free Finish					
# of Channels	Leads	Package	Ordering Part Number <sup>1</sup>	Part Marking	
6	8	SOIC-8	CM1213-06SM	D136	
6	8	MSOP-8	CM1213-06MR	D137	
8	10	MSOP-10	CM1213-08MR	D138	

Note 1: Parts are shipped in Tape & Reel form unless otherwise specified.

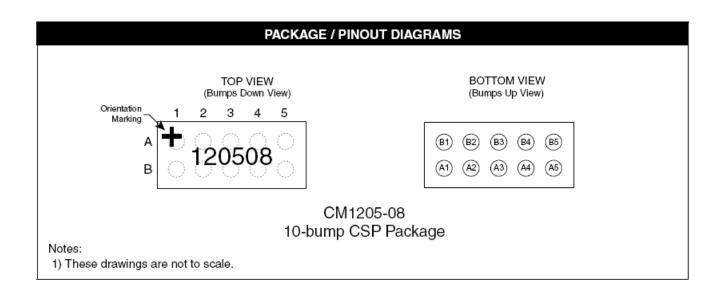
# **Specifications**

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	RATING	UNITS			
Operating Supply Voltage (V <sub>P</sub> - V <sub>N</sub> )	6.0	V			
Operating Temperature Range	-40 to +85	°C			
Storage Temperature Range	-65 to +150	°C			
DC Voltage at any channel input	$(V_N - 0.5)$ to $(V_P + 0.5)$	V			

STANDARD OPERATING CONDITIONS					
PARAMETER	RATING	UNITS			
Operating Temperature Range	-40 to +85	°C			
Package Power Rating MSOP-8 Package (CM1213-06MR) MSOP-10 Package (CM1213-08MR) SOIC-8 Package (CM1213-06SM)	400 400 600	mW mW mW			

	ELECTRICAL OF	PERATING CHARACTERISTICS	S <sup>(SEE NOT</sup>	E 1)		
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V <sub>P</sub>	Operating Supply Voltage (V <sub>P</sub> -V <sub>N</sub> )			3.3	5.5	V
I <sub>P</sub>	Operating Supply Current	$(V_{P}-V_{N})=3.3V$			8.0	μΑ
V <sub>F</sub>	Diode Forward Voltage Top Diode Bottom Diode	I <sub>F</sub> = 8mA; T <sub>A</sub> =25 ℃	0.60 0.60	0.80 0.80	0.95 0.95	V
I <sub>LEAK</sub>	Channel Leakage Current	$T_{A}=25 ^{\circ}\text{C}; V_{P}=5V, V_{N}=0V$		±0.1	±1.0	μΑ
C <sub>IN</sub>	Channel Input Capacitance	At 1 MHz, $V_p=3.3V$ , $V_N=0V$ , $V_{IN}=1.65V$ ;		1.0	1.5	pF
$\Delta C_{\scriptscriptstyleIN}$	Channel Input Capacitance Matching	At 1 MHz, $V_p=3.3V$ , $V_N=0V$ , $V_{IN}=1.65V$ ;		0.02		pF
C <sub>MUTUAL</sub>	Mutual Capacitance between signal pin and adjacent signal pin	At 1 MHz, $V_p=3.3V$ , $V_N=0V$ , $V_{IN}=1.65V$ ;		0.11		pF
V <sub>ESD</sub>	ESD Protection Peak Discharge Voltage at any channel input, in system Contact discharge per IEC 61000-4-2 standard	Notes 3 and 4; T <sub>A</sub> =25 °C	±8			kV
V <sub>CL</sub>	Channel Clamp Voltage Positive Transients Negative Transients	$T_A = 25 ^{\circ}\text{C}$ , $I_{PP} = 1 ^{\circ}\text{A}$ , $t_P = 8/20 ^{\circ}\text{uS}$ ; Note 4		+8.8 -1.4		V V
R <sub>DYN</sub>	Dynamic Resistance Positive Transients Negative Transients	$I_{pp}$ = 1A, $t_p$ = 8/20uS Any I/O pin to Ground; Note 4		0.7 0.4		Ω

Note 1: All parameters specified at  $T_A$  = -40 °C to +85 °C unless otherwise noted. Note 2: Human Body Model per MIL-STD-883, Method 3015,  $C_{Discharge}$  = 100pF,  $R_{Discharge}$  = 1.5K $\Omega$ ,  $V_P$  = 3.3V,  $V_R$  grounded. Note 3: Standard IEC 61000-4-2 with  $C_{Discharge}$  = 150pF,  $R_{Discharge}$  = 330 $\Omega$ ,  $V_P$  = 3.3V,  $V_R$  grounded. Note 4: These measurements performed with no external capacitor on  $V_P$  ( $V_P$  floating).



## **Ordering Information**

	PART NUM	MBERING INFORMATION	
Bumps	Package	Ordering Part Number <sup>1</sup>	Part Marking
10	CSP	CM1205-08CP	120508

Note 1: Parts are shipped in Tape & Reel form unless otherwise specified.

#### **Specifications**

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	RATING	UNITS			
Storage Temperature Range	-65 to +150	°C			

STANDARD OPERATING CONDITIONS					
PARAMETER	RATING	UNITS			
Operating Temperature Range	-40 to +85	S			

# CM1213

## Specifications (cont'd)

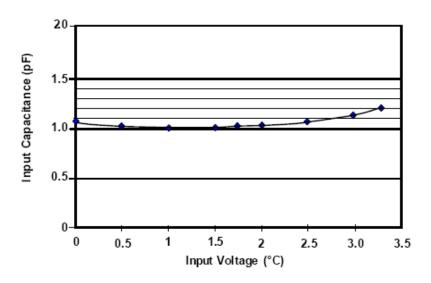
	ELECTRICAL OPERATING CHARACTERISTICS <sup>1</sup>							
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS		
V <sub>REV</sub>	Reverse Standoff Voltage	$I_{\text{DIODE}} = 10 \mu A$		6.0		V		
I <sub>LEAK</sub>	Leakage Current	V <sub>IN</sub> =3.3V DC			100	nA		
V <sub>SIG</sub>	Signal Clamp Voltage Positive Clamp Negative Clamp	I <sub>LOAD</sub> = 10mA	5.6 -1.2	6.8 -0.8	8.0 -0.4	V		
V <sub>ESD</sub>	In-system ESD Withstand Voltage a) Human Body Model, MIL-STD-883, Method 3015 b) Contact Discharge per IEC 61000-4-2 Level 4	Notes 2 & 3	<u>+</u> 30 <u>+</u> 25			kV kV		
V <sub>CL</sub>	Clamping Voltage during ESD Discharge MIL-STD-883 (Method 3015), 8kV Positive Transients Negative Transients	Notes 2 & 3		+12		V		
С	Channel Capacitance	At 2.5V DC, <i>f</i> = 1MHz, Note 3		39	47	pF		

Note 1:  $T_A=25$  °C unless otherwise specified. GND in this document refers to the lower supply voltage. Note 2: ESD applied to channel pins with respect to GND, one at a time. All other channels are open. All GND pins tied to ground.

Note 3: These parameters are guaranteed by design and characterization.

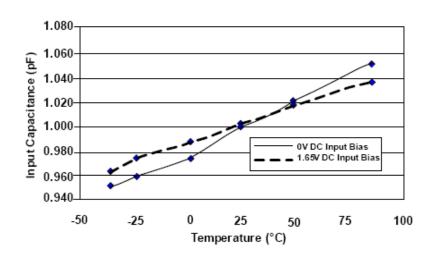
# **Performance Information**

**Input Channel Capacitance Performance Curves** 



Typical Variation of CIN vs. VIN

(f=1MHz, Vp = 3.3V, VN = 0V, 0.1  $\mu F$  chip capacitor between Vp and VN, 25°C)



Typical Variation of  $C_{\text{IN}}$  vs. Temp

(f=1MHz,  $V_{IN}$ =30mV,  $V_{P}$  = 3.3V,  $V_{N}$  = 0V, 0.1  $\mu$ F chip capacitor between  $V_{P}$  and  $V_{N}$ )

# **Performance Information (Cont'd)**

Typical Filter Performance (nominal conditions unless specified otherwise, 50 Ohm Environment)

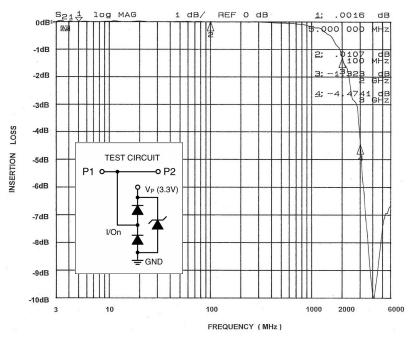


Figure 1. Insertion Loss (S21) VS. Frequency (0V DC Bias, V<sub>p</sub>=3.3V)

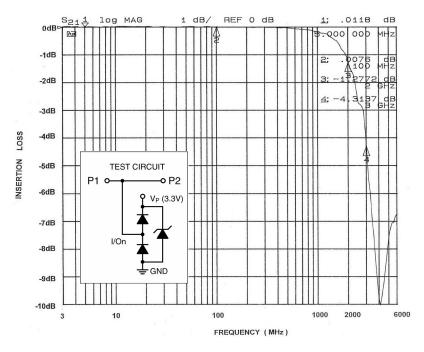


Figure 2. Insertion Loss (S21) VS. Frequency (2.5V DC Bias, V<sub>p</sub>=3.3V)

## **Application Information**

#### **Design Considerations**

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Application of Positive ESD Pulse between Input Channel and Ground, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to the power supply is represented by  $L_1$  and  $L_2$ . The voltage  $V_{CL}$  on the line being protected is:

$$V_{cL}$$
 = Fwd voltage drop of  $D_1$  +  $V_{SUPPLY}$  +  $L_1$  x d( $I_{ESD}$  ) / dt +  $L_2$  x d( $I_{ESD}$ ) / dt

where  $I_{ESD}$  is the ESD current pulse, and  $V_{SUPPLY}$  is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000-4-2 standard results in a current pulse that rises from zero to 30 Amps in 1ns. Here  $d(I_{ESD})/dt$  can be approximated by  $\Delta I_{ESD}/\Delta t$ , or  $30/(1x10^{-9})$ . So just 10nH of series inductance (L, and L<sub>2</sub> combined) will lead to a 300V increment in  $V_{CL}$ !

Similarly for negative ESD pulses, parasitic series inductance from the  $V_N$  pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

The CM1213 has an integrated Zener diode between  $V_p$  and  $V_N$ . This greatly reduces the effect of supply rail inductance  $L_z$  on  $V_{CL}$  by clamping  $V_p$  at the breakdown voltage of the Zener diode. However, for the lowest possible  $V_{CL}$ , especially when  $V_p$  is biased at a voltage significantly below the Zener breakdown voltage, it is recommended that a  $0.22\mu F$  ceramic chip capacitor be connected between  $V_p$  and the ground plane.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the  $V_p$  pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

#### **Additional Information**

See also California Micro Devices Application Note AP209, "Design Considerations for ESD Protection", in the Applications section at www.calmicro.com.

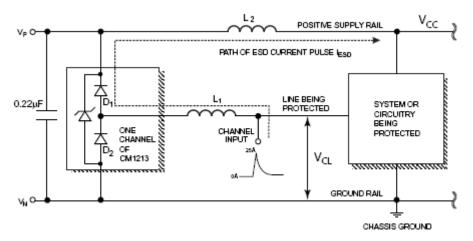


Figure 3. Application of Positive ESD Pulse between Input Channel and Ground

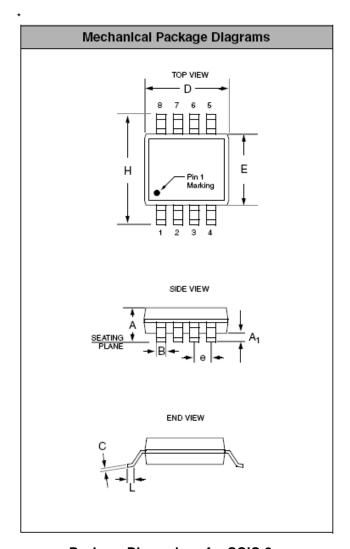
# CM1213

## **Mechanical Details**

The CM1213 is available in MSOP-8, SOIC-8, and MSOP-10 packages with a lead-free finishing. **SOIC-8 Mechanical Specifications** 

The CM1213-06SM is supplied in an 8-pin SOIC package. Dimensions are presented below.

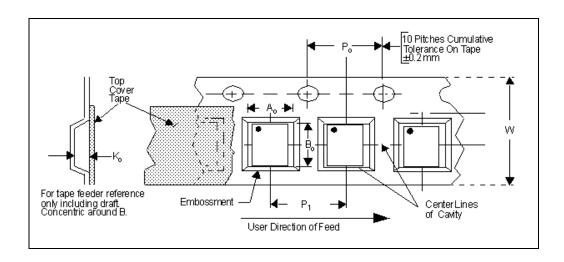
PACKAGE DIMENSIONS						
Package		SC	OIC			
Pins			8			
Dimensions	Millir	neters	Inc	hes		
Dimensions	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A,	0.10	0.25	0.004	0.010		
В	0.33	0.013	0.020			
С	0.19	0.25	0.007	0.010		
D	4.80	5.00	0.189	0.197		
E	3.80	4.19	0.150	0.165		
е	1.27	BSC	0.050	) BSC		
Н	5.80	6.20	0.228	0.244		
L	0.40	1.27	0.016	0.050		
# per tape and reel	2500 pieces					
	Controlling dimension: inches					



Package Dimensions for SOIC-8

#### **Tape and Reel Specifications**

PART NUMBER	PACKAGE SIZE (mm)	POCKET SIZE (mm) B <sub>o</sub> X A <sub>o</sub> X K <sub>o</sub>	TAPE WIDTH W	REEL DIAMETER	QTY PER REEL	P <sub>o</sub>	P <sub>1</sub>
CM1213-06SM	4.90 X 6.00 X 1.55	5.30 X 6.50 X 2.10	12mm	330mm (13")	2500	4mm	8mm

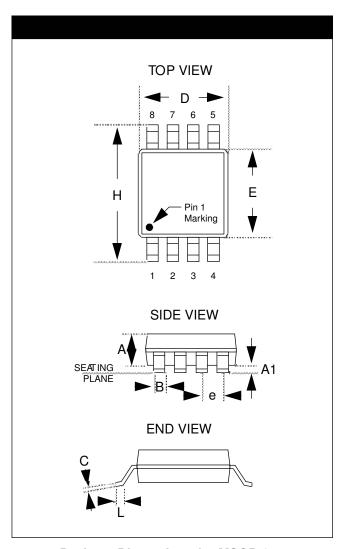


# **Mechanical Details (Cont'd)**

## **MSOP-8 Mechanical Specifications:**

The CM1213-06MR is supplied in an 8-pin MSOP package. Dimensions are presented below.

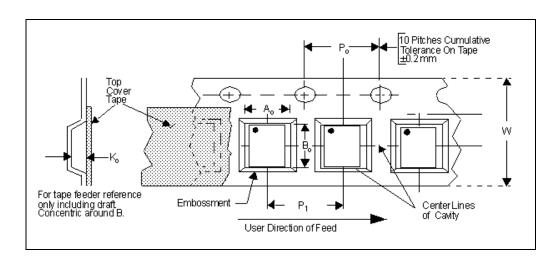
PACKAGE DIMENSIONS						
Package	MSOP					
Pins	8					
Dimensions	Millir	neters	Inches			
Dimensions	Min	Max	Min	Max		
A	0.75	0.95	0.030	0.037		
<b>A</b> 1	0.05	0.15	0.002	0.006		
В	0.28	0.38	0.011	0.015		
С	0.13	0.23	0.005	0.009		
D	2.90	3.10	0.114	0.122		
E	2.90	3.10	0.114	0.122		
е	0.65	BSC	0.026 BSC			
Н	4.90 BSC		0.193 BSC			
L	0.40	0.70	0.016	0.028		
# per tape and reel	4000 pieces					
Controlling dimension: millimeters						



Package Dimensions for MSOP-8

#### **Tape and Reel Specifications**

PART NUMBER	PACKAGE SIZE (mm)	POCKET SIZE (mm) B <sub>o</sub> X A <sub>o</sub> X K <sub>o</sub>	TAPE WIDTH W	REEL DIAMETER	QTY PER REEL	P₀	P <sub>1</sub>
CM1213-06MR	3.00 X 3.00 X 0.85	3.3 X 5.3 X1.3	12mm	330mm (13")	4000	4mm	8mm

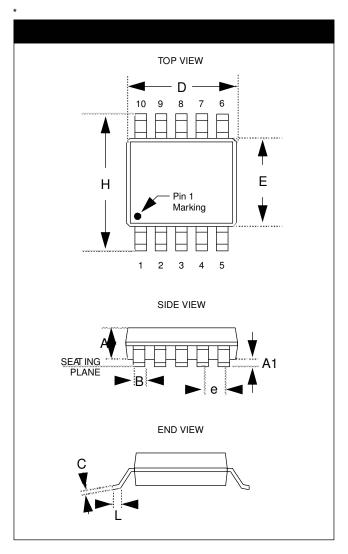


# Mechanical Details (cont'd)

## **MSOP-10 Mechanical Specifications**

The CM1213-08MR is supplied in a 10-pin MSOP package. Dimensions are presented below.

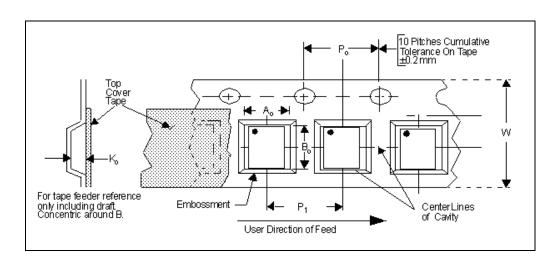
PACKAGE DIMENSIONS						
Package	MSOP					
Pins	10					
Dimensions	Millir	neters	Inches			
	Min	Max	Min	Max		
Α	0.75	0.95	0.028	0.038		
<b>A</b> 1	0.05	0.15	0.002	0.006		
В	0.17	0.33	0.007	0.013		
С	0.13	0.23	0.005	0.009		
D	2.90	3.10	0.114	0.122		
E	2.90	3.10	0.114	0.122		
е	0.50 BSC		0.0196 BSC			
Н	4.90 BSC		0.193 BSC			
L	0.40	0.70	0.0137	0.029		
# per tape and reel	4000					
Controlling dimension: inches						



Package Dimensions for MSOP-10

#### **Tape and Reel Specifications**

PART NUMBER	PACKAGE SIZE (mm)	POCKET SIZE (mm) B <sub>o</sub> X A <sub>o</sub> X K <sub>o</sub>	TAPE WIDTH W	REEL DIAMETER	QTY PER REEL	P <sub>o</sub>	P,
CM1213-08MR	3.00 X 3.00 X 0.85	3.3 X 5.3 X1.3	12mm	330mm (13")	4000	4mm	8mm



## CM1213

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